

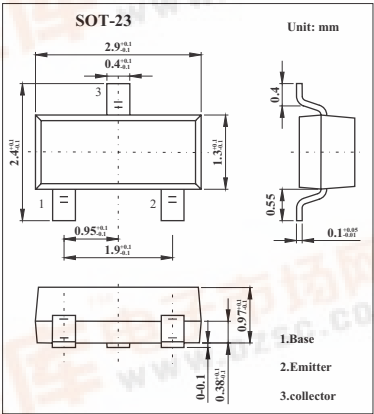
SMD Type

Transistors

PNP General Purpose Transistor
2PB710A

■ Features

- High current (max. 500 mA)
- Low voltage (max. 50 V).



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	VCBO	-60	V
Collector-emitter voltage	VCEO	-50	V
Emitter-base voltage	VEBO	-5	V
Collector current (DC)	IC	-500	mA
Peak collector current	ICM	-1	A
Peak base current	IBM	-200	mA
Total power dissipation Tamb≤25℃; *	Ptot	250	mW
Storage temperature	Tstg	-65 to +150	℃
Junction temperature	Tj	150	℃
Operating ambient temperature	Tamb	-65 to +150	℃
Thermal resistance from junction to ambient *	Rth j-a	500	K/W

* Transistor mounted on an FR4 printed-circuit board.



2PB710A

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	I _E = 0; V _{CB} = -60 V			-10	nA
		I _E = 0; V _{CB} = -60 V; T _j = 150 °C			-5	μA
Emitter cut-off current	I _{EBO}	I _C = 0; V _{EB} = -5 V			-10	nA
DC current gain 2PB710AQ 2PB710AR 2PB710AS	h _{FE}	I _C = -150 mA; V _{CE} = -10 V*	85		170	
			120		240	
			170		340	
DC current gain		I _C = -500 mA; V _{CE} = -10 V; *	40			
Collector-emitter saturation voltage	V _{CEsat}	I _C = -300 mA; I _B = -30 mA *			-600	mV
Base-emitter saturation voltage	V _{BEsat}	I _C = -300 mA; I _B = -30 mA *			-1.5	V
Collector capacitance	C _c	I _E = i _e = 0; V _{CB} = -10 V; f = 1 MHz			15	pF
Transition frequency 2PB710AQ 2PB710AR 2PB710AS	f _T	I _C = -50 mA; V _{CE} = -10 V; f = 100 MHz*	100			MHz
			120			
			140			

*. Pulse test: t_p ≤ 300 μs; δ ≤ 0.02.

■ Marking

Type Number	2PB710AQ	2PB710AR	2PB710AS
Marking	DQ	DR	DS